

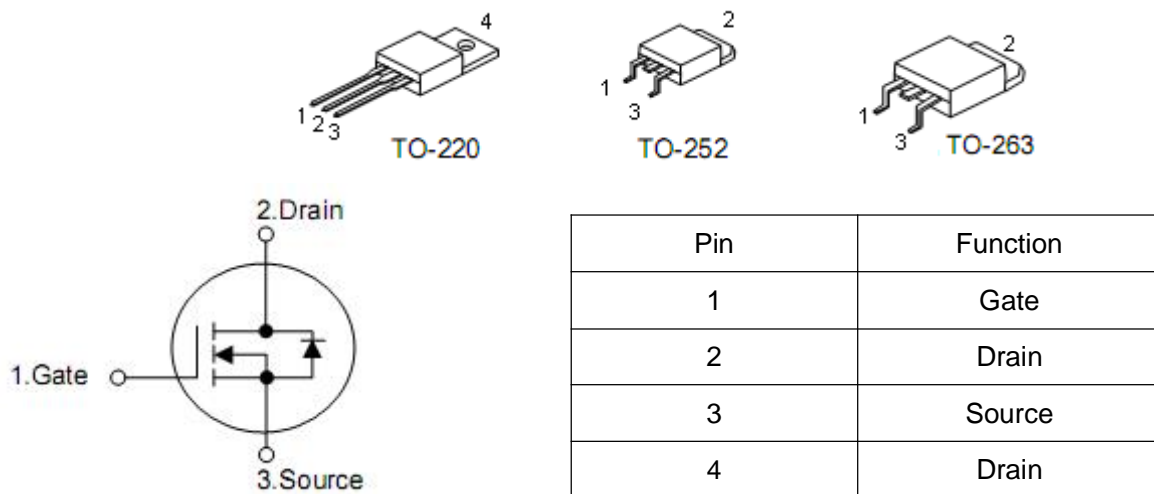
## 1. Features

- n  $R_{DS(on)}=9m\Omega$  (typ.) @  $V_{GS}=10V$
- n 100% avalanche tested
- n Reliable and rugged
- n Lead free and green device available (RoHS Compliant)

## 2. Applications

- n Switching application
- n Power management for inverter systems

## 3.Symbol



#### 4. Absolute maximum ratings

( $T_A=25^{\circ}\text{C}$ , unless otherwise noted)

| Parameter                    | Symbol     | Rating                       |        | Units              |   |
|------------------------------|------------|------------------------------|--------|--------------------|---|
|                              |            | To-220/263                   | To-252 |                    |   |
| Drain-source voltage         | $V_{DSS}$  | 100                          |        | V                  |   |
| Gate-source voltage          | $V_{GSS}$  | $\pm 25$                     |        | V                  |   |
| Maximum junction temperature | $T_J$      | 175                          |        | $^{\circ}\text{C}$ |   |
| Storage temperature range    | $T_{STG}$  | -55 to 175                   |        | $^{\circ}\text{C}$ |   |
| Continuous drain current     | $I_{D^3}$  | $T_C=25^{\circ}\text{C}$     | 75     | 65                 | A |
|                              |            | $T_C=100^{\circ}\text{C}$    | 51     | 44                 | A |
| Pulsed drain current         | $I_{DP^4}$ | $T_C=25^{\circ}\text{C}$ 219 |        | A                  |   |
| Avalanche current            | $I_{AS^5}$ | 30                           |        | A                  |   |
| Avalanche energy             | $E_{AS^5}$ | 225                          |        | mJ                 |   |
| Maximum power dissipation    | $P_D$      | $T_C=25^{\circ}\text{C}$     | 166    |                    | W |
|                              |            | $T_C=100^{\circ}\text{C}$    | 83     |                    | W |

#### 5. Thermal characteristics

| Parameter                            | Symbol          | Rating | Unit                        |
|--------------------------------------|-----------------|--------|-----------------------------|
| Thermal resistance, Junction-ambient | $R_{\theta JA}$ | 62.5   | $^{\circ}\text{C}/\text{W}$ |
| Thermal resistance, Junction-case    | $R_{\theta JC}$ | 0.9    | $^{\circ}\text{C}/\text{W}$ |

## 6. Electrical characteristics

( $T_A=25^\circ\text{C}$ , unless otherwise noted)

| Parameter                        | Symbol         | Test Conditions  | Min | Typ  | Max       | Units         |
|----------------------------------|----------------|--|-----|------|-----------|---------------|
| Drain-source breakdown voltage   | $BV_{DSS}$     | $V_{GS}=0V, I_{DS}=250\text{Ma}$                         | 100 | -    | -         | V             |
| Zero gate voltage drain current  | $I_{DSS}$      | $V_{DS}=80V, V_{GS}=0V$                                  | -   | -    | 1         | $\mu\text{A}$ |
|                                  |                | $T_J=125^\circ\text{C}$                                  | -   | -    | 20        |               |
| Gate threshold voltage           | $V_{GS(th)}$   | $V_{DS}=V_{GS}, I_{D}=250\mu\text{A}$                    | 2.0 | 3.0  | 4.0       | V             |
| Gate leakage current             | $I_{GSS}$      | $V_{GS}=\pm 25V, V_{DS}=0V$                              | -   | -    | $\pm 100$ | nA            |
| Drain-source on-state resistance | $R_{DS(on)}^1$ | $V_{GS}=10V, I_{DS}=50A$<br>(TO-220\TO-263)              | -   | 9    | 11        | m $\Omega$    |
|                                  |                | $V_{GS}=10V, I_{DS}=50A$<br>(TO-252)                     | -   | 9    | 14        |               |
| Gate resistance                  | $R_g$          | $V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$                    | -   | 1.2  | -         | $\Omega$      |
| Diode forward voltage            | $V_{SD}^1$     | $I_{SD}=50A, V_{GS}=0V$                                  | -   | -    | 1.3       | V             |
| Reverse recovery time            | $t_{rr}$       | $I_{SD}=50A,$<br>$di_{SD}/dt=100A/\mu\text{s}$           | -   | 46   | -         | nS            |
| Reverse recovery charge          | $Q_{rr}$       |  | -   | 86   | -         | nC            |
| Input capacitance                | $C_{iss}$      | $V_{DS}=25V, V_{GS}=0V,$<br>$f=1\text{MHz}$              | -   | 2946 | -         | pF            |
| Output capacitance               | $C_{oss}$      |  | -   | 339  | -         |               |
| Reverse transfer capacitance     | $C_{rss}$      |  | -   | 179  | -         |               |
| Turn-on delay time               | $t_{d(on)}$    | $V_{DD}=50V, I_{DS}=30A,$<br>$R_G=6.8\Omega, V_{GS}=10V$ | -   | 15   | -         | ns            |
| Rise time                        | $t_r$          |  | -   | 108  | -         |               |
| Turn-off delay time              | $t_{d(off)}$   |  | -   | 51   | -         |               |
| Fall time                        | $t_f$          |  | -   | 59   | -         |               |
| Total gate charge                | $Q_g$          | $V_{DS}=50V, V_{GS}=10V$<br>$I_{DS}=30A$                 | -   | 60   | -         | nC            |
| Gate-source charge               | $Q_{gs}$       |  | -   | 13.7 | --        |               |
| Gate-drain charge                | $Q_{gd}$       |  | -   | 22.8 | --        |               |

Note : 1. Pulse test; pulse width  $\leq 300\mu\text{s}$  duty cycle  $\leq 2\%$ .

2. Guaranteed by design, not subject to production testing.

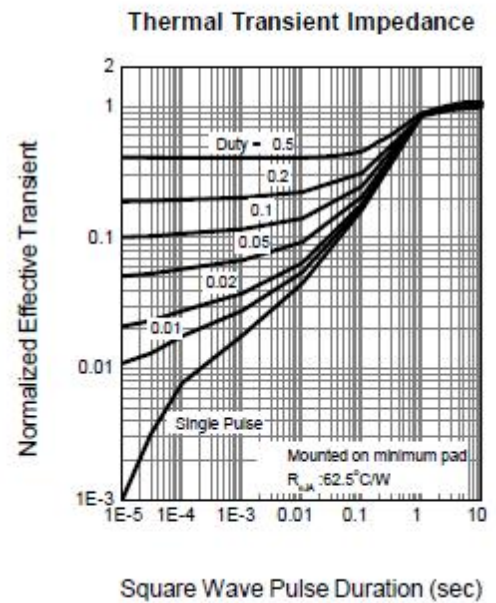
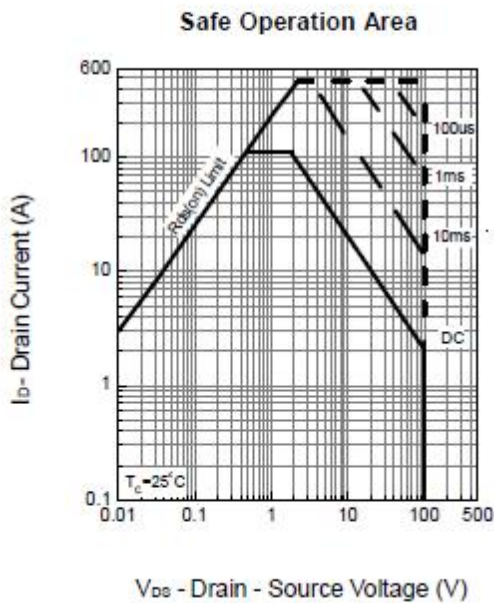
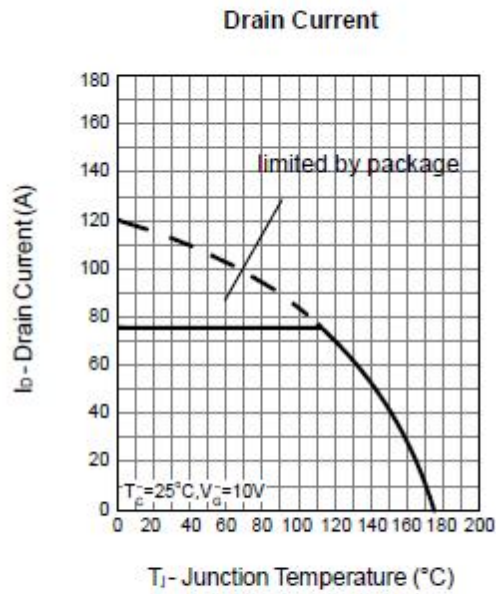
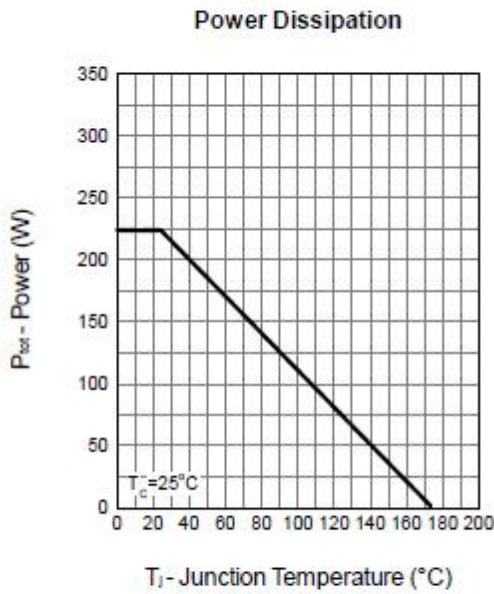
3. Package limitation current is 55A.

4. Repetitive rating, pulse width limited by max junction temperature.

5. Starting  $T_J=25^\circ\text{C}$ ,  $L=0.5\text{mH}$ ,  $I_{AS}=30A$ .

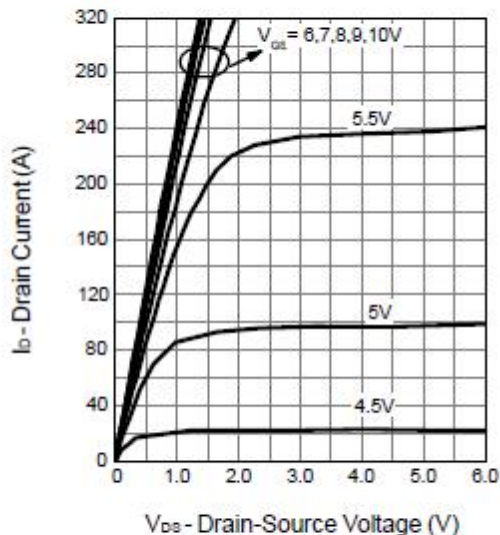
**7. Test circuits and waveforms**

**Typical Operating Characteristics**

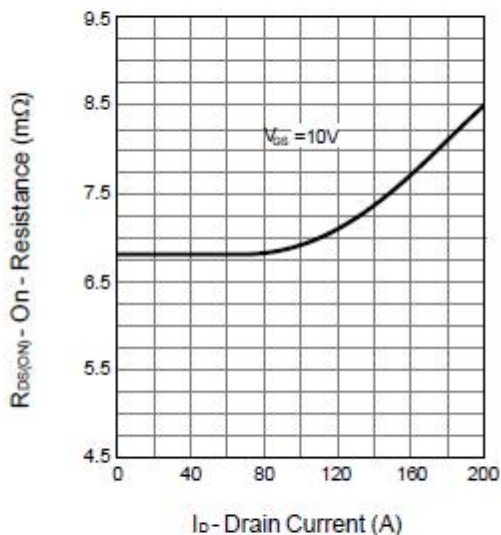


**Typical Operating Characteristics (Cont.)**

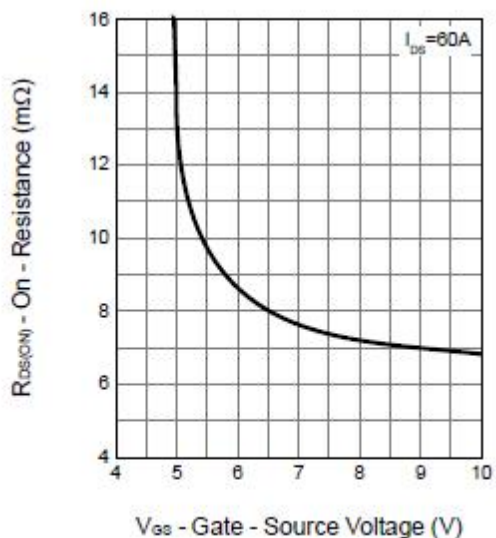
Output Characteristics



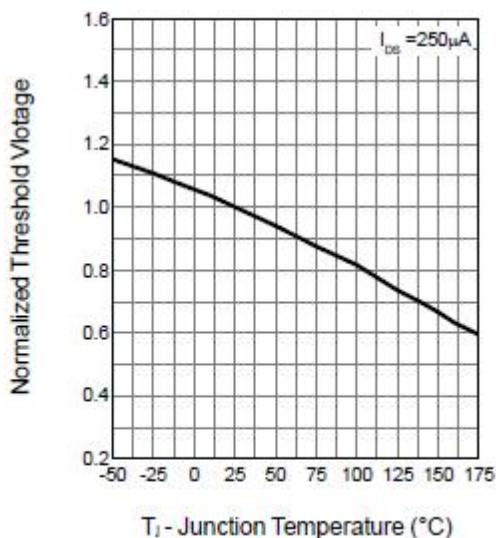
Drain-Source On Resistance



Drain-Source On Resistance

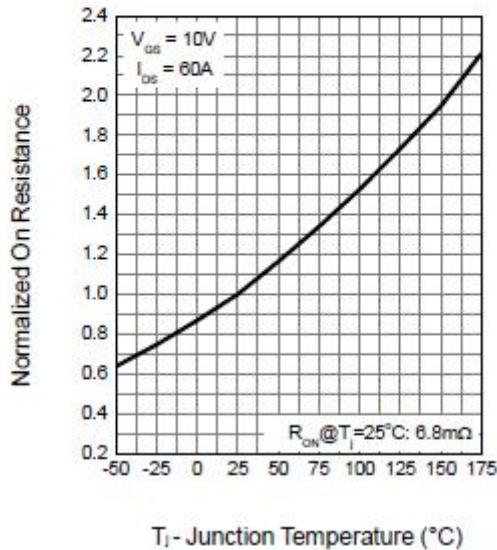


Gate Threshold Voltage

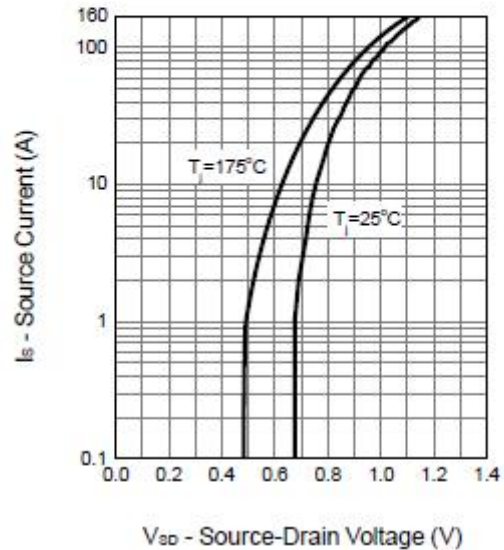


**Typical Operating Characteristics (Cont.)**

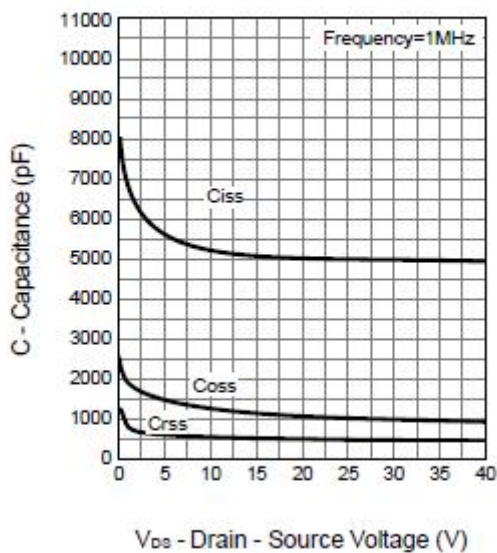
**Drain-Source On Resistance**



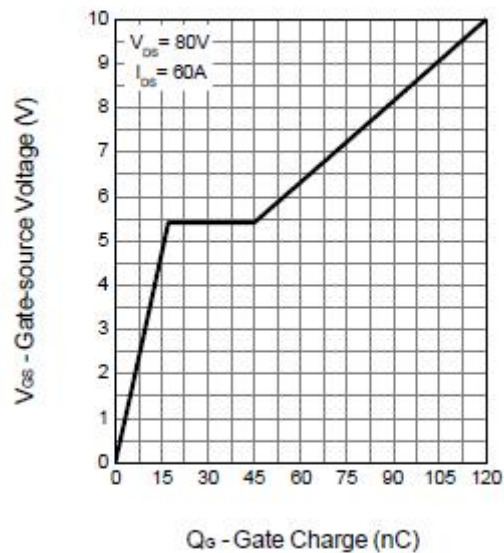
**Source-Drain Diode Forward**



**Capacitance**



**Gate Charge**



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